

Correspondence

Correction to "Optimization of the Specific On-Resistance of the COOLMOS™"

Xing-Bi Chen and Johnny K. O. Sin

In the above paper,¹ please note the following correction. Table I in the paper should be replaced by Table I.

COOLMOS is a trademark name from Siemens, AG, Germany.

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



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¹X.-B. Chen and J. K. O. Sin, *IEEE Trans. Electron Devices*, vol. 48, pp. 344–348, Feb. 2001.

TABLE I
GEOMETRICAL AND MODELING PARAMETERS OF THE CB-STRUCTURE
DESIGNED USING DIFFERENT CELL PATTERNS. (DERIVATIONS OF THE VARIOUS
MODEL PARAMETERS ARE GIVEN IN A PRIOR PUBLICATION)*

Layout	Interdigitated	Hexagonal	Square	Lattice
Pattern				
a	0.5	0.36	0.465	0.5
c _p	0.371	0.184	0.205	0.205
c _n	0.371	0.104	0.178	0.205
d	0.5	0.113	0.172	0.237
f _p	16.1	7.99	8.91	8.91
f _n	16.1	4.52	7.73	8.91
f _{cp}	2.42	1.94	0.742	1.15
f _{cn}	2.42	0.42	0.833	1.15
f _c = f _{cp} + f _{cn}	4.84	2.36	1.56	2.3
g	1.910	0.827	1.05	1.11
g _c	2.50	0.881	1.02	1.27

*X. Chen, "Optimum design parameters for different patterns of composite buffer (CB) structure," *Chin. J. Electron.*, vol. 9, pp. 6–10, 2000.